

BUK7K89-100E

Dual N-channel 100 V, 82.5 mΩ standard level MOSFET 2 September 2015 Product data sheet

1. **General description**

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. **Features and benefits**

- **Dual MOSFET**
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. **Applications**

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	13	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	38	W	
Static characte	Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	61	82.5	mΩ	
Dynamic characteristics FET1 and FET2								
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	5.3	-	nC	



Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	j j j j	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7K89-100E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K89-100E	78910E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	100	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	38	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	13	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	9	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	51	Α

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Dual N-channel 100 V, 82.5 mΩ standard level MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	in diode FET1 and FET2					
I _S	source current	T _{mb} = 25 °C		-	13	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	51	Α
Avalanche Ruggedness FET1 and FET2						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 13 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	19.5	mJ

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

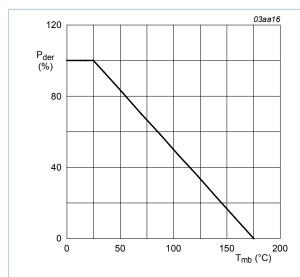


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

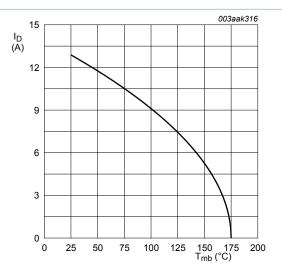


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

Dual N-channel 100 V, 82.5 mΩ standard level MOSFET

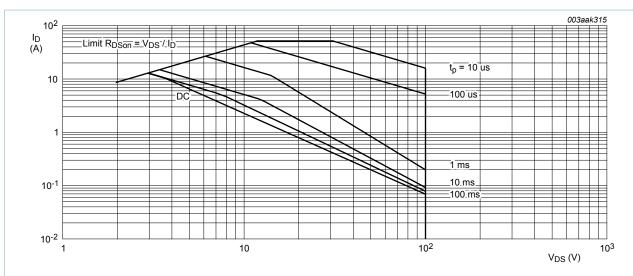


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



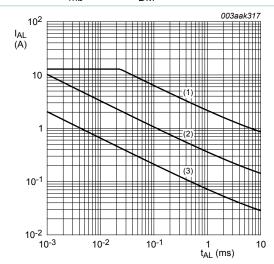


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

9. Thermal characteristics

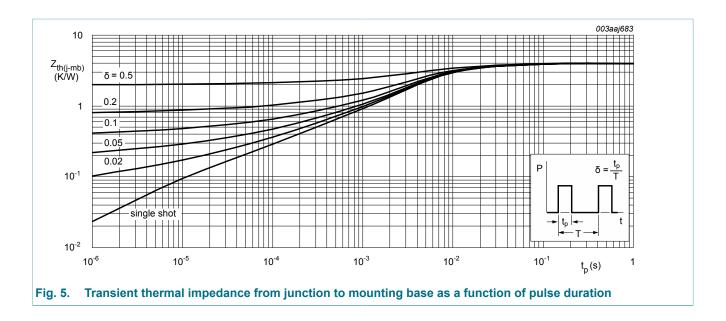
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	3.96	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

BUK7K89-100E

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Dual N-channel 100 V, 82.5 m Ω standard level MOSFET



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics FET1 and FET2					
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	90	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	61	82.5	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-	168	228	mΩ
Dynamic ch	aracteristics FET1 and FE	T2	'			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V;	-	13.6	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	2.8	-	nC
Q_GD	gate-drain charge		-	5.3	-	nC

Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	608	811	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	74	89	pF
C _{rss}	reverse transfer capacitance			-	51	70	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 15 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	4.6	-	ns
t _r	rise time			-	5.9	-	ns
t _{d(off)}	turn-off delay time			-	12	-	ns
t _f	fall time			-	7.3	-	ns
Source-dra	in diode FET1 and FET2	1	l				
V _{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	31.6	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$		-	39.1	-	nC

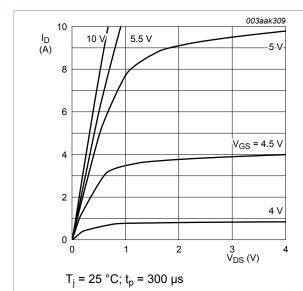


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

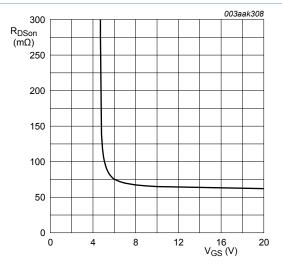


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

6/13

Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

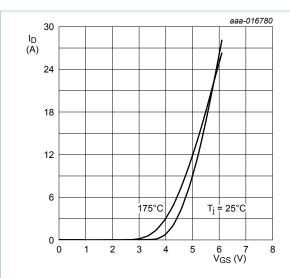


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



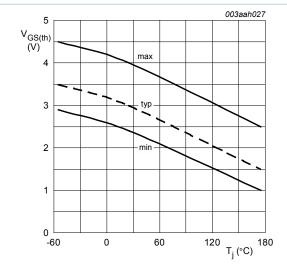


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}

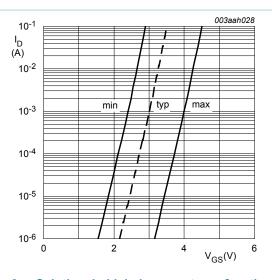
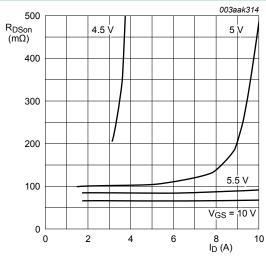


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

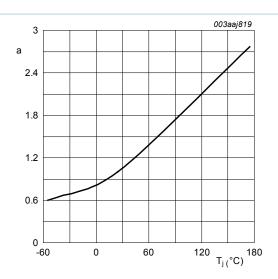


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

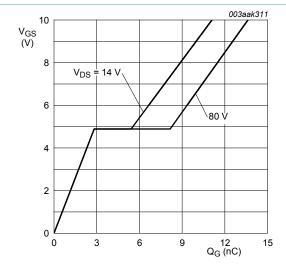


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_i = 25^{\circ}C; I_D = 5A$$

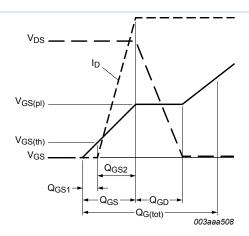


Fig. 13. Gate charge waveform definitions

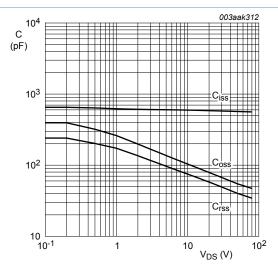


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

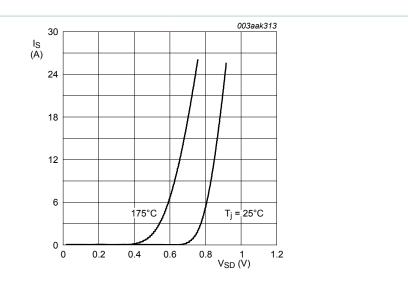
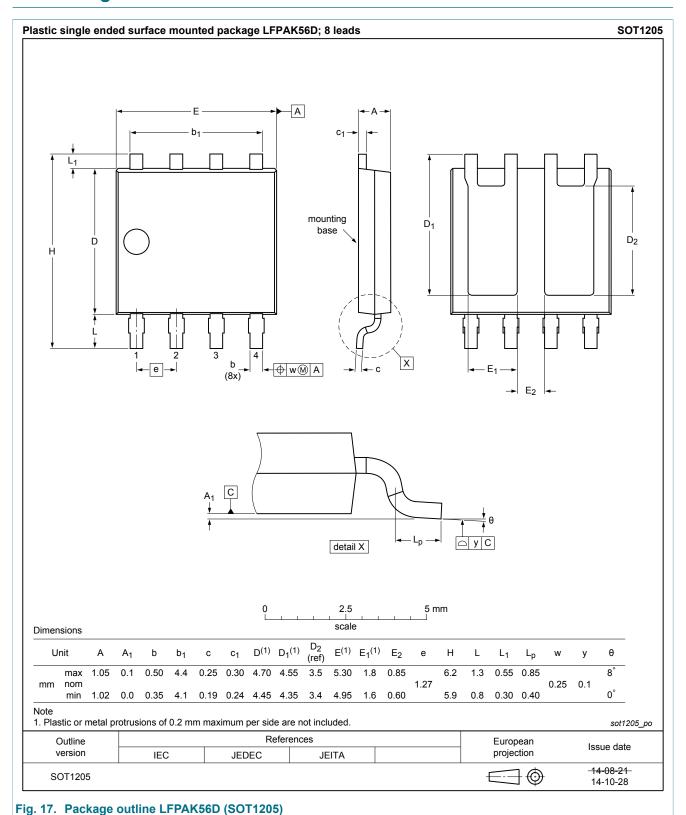


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

Dual N-channel 100 V, 82.5 mΩ standard level MOSFET

11. Package outline



BUK7K89-100E

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Dual N-channel 100 V, 82.5 mΩ standard level MOSFET

12. Legal information

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Document status [1][2]	Product status [3]	Definition
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Dual N-channel 100 V, 82.5 m Ω standard level MOSFET

13. Contents

1	General description	1
2	Features and benefits	
3	Applications	1
4	Quick reference data	
5	Pinning information	
6	Ordering information	
7	Marking	
8	Limiting values	
9	Thermal characteristics	
10	Characteristics	
11	Package outline	
12	Legal information	
12.1	Data sheet status	
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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